

n-GaN/p-GaN/u-GaN Wafer



We are supplying n-GaN, p-GaN, u-GaN which are produced with epitaxial growth using our proprietary technology.

For your future request, we are offering other designed GaN.wafer, InGaN and AlGaIn.

Substrate materials for MOCVD GaN on Sapphire

SPECIFICATIONS

Epi wafer diameter	2 inch
Epi layer	GaN
Thickness of GaN epilayer	2-10 μm
Structure of GaN epilayer	Wurtzite
Orientation of GaN layer	(0001)
Conductivity	N-type P-type undoped-type
Surface	as grown
Substrate	Sapphire
Substrate orientation	(0001) on-axis

*No buffer layer is required.